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### Understanding [Embedded - Microprocessors](#)

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

### Applications of [Embedded - Microprocessors](#)

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

#### Details

Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	266MHz
Co-Processors/DSP	Communications; QUICC Engine, Security; SEC
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (1)
SATA	-
USB	USB 1.x (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	740-LBGA
Supplier Device Package	740-TBGA (37.5x37.5)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8360ezuaddh">https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8360ezuaddh</a>

wide range of protocols including ATM, Ethernet, HDLC, and POS. The QUICC Engine module's enhanced interworking eases the transition and reduces investment costs from ATM to IP based systems. The other major features include a dual DDR SDRAM memory controller for the MPC8360E, which allows equipment providers to partition system parameters and data in an extremely efficient way, such as using one 32-bit DDR memory controller for control plane processing and the other for data plane processing. The MPC8358E has a single DDR SDRAM memory controller. The MPC8360E/58E also offers a 32-bit PCI controller, a flexible local bus, and a dedicated security engine.

This figure shows the MPC8360E block diagram.

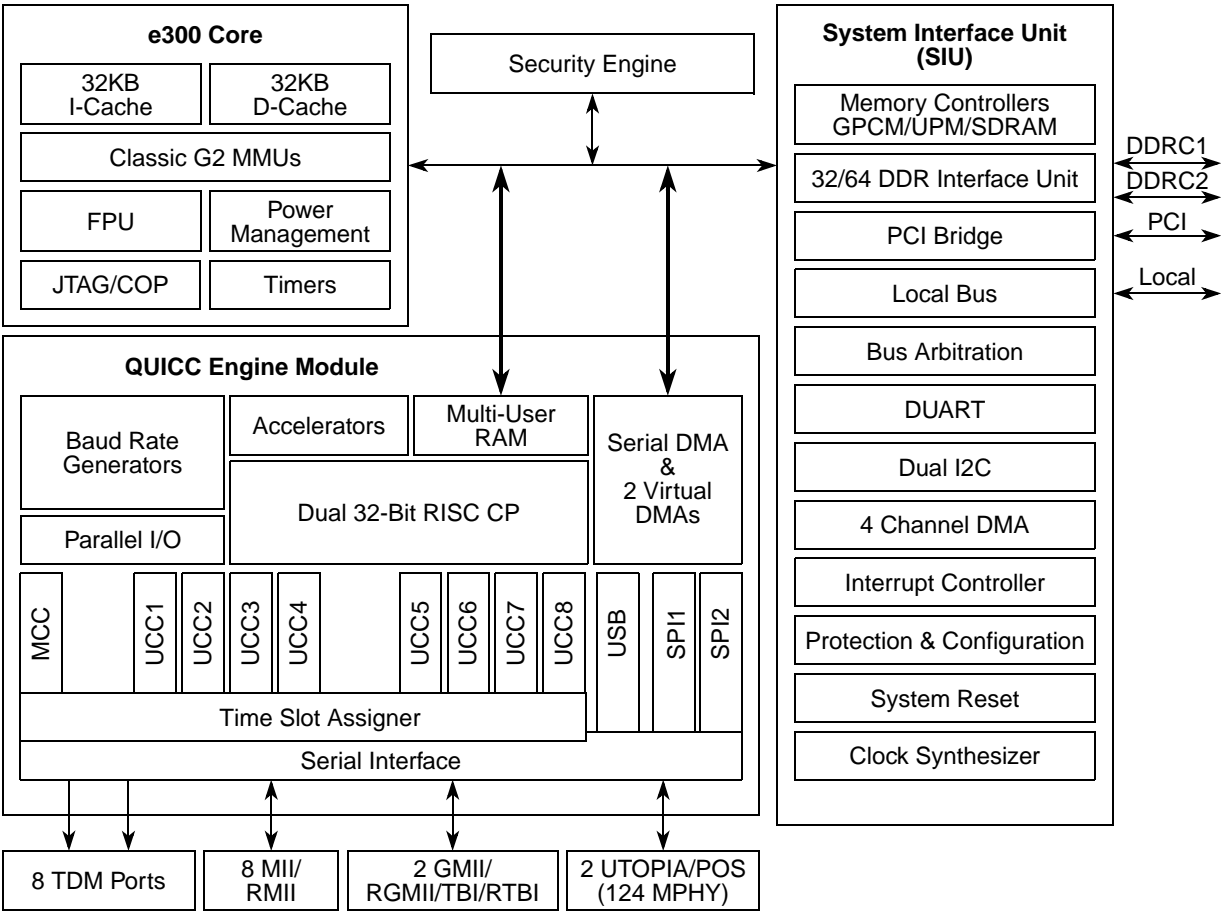


Figure 1. MPC8360E Block Diagram

- 10/100 Mbps Ethernet/IEEE Std. 802.3™ CDMA/CS interface through a media-independent interface (MII, RMII, RGMII)<sup>1</sup>
- 1000 Mbps Ethernet/IEEE 802.3 CDMA/CS interface through a media-independent interface (GMII, RGMII, TBI, RTBI) on UCC1 and UCC2
- 9.6-Kbyte jumbo frames
- ATM full-duplex SAR, up to 622 Mbps (OC-12/STM-4), AAL0, AAL1, and AAL5 in accordance ITU-T I.363.5
- ATM AAL2 CPS, SSSAR, and SSTED up to 155 Mbps (OC-3/STM-1) Mbps full duplex (with 4 CPS packets per cell) in accordance ITU-T I.366.1 and I.363.2
- ATM traffic shaping for CBR, VBR, UBR, and GFR traffic types compatible with ATM forum TM4.1 for up to 64-Kbyte simultaneous ATM channels
- ATM AAL1 structured and unstructured circuit emulation service (CES 2.0) in accordance with ITU-T I.163.1 and ATM Forum af-vtoa-00-0078.000
- IMA (Inverse Multiplexing over ATM) for up to 31 IMA links over 8 IMA groups in accordance with the ATM forum AF-PHY-0086.000 (Version 1.0) and AF-PHY-0086.001 (Version 1.1)
- ATM Transmission Convergence layer support in accordance with ITU-T I.432
- ATM OAM handling features compatible with ITU-T I.610
- PPP, Multi-Link (ML-PPP), Multi-Class (MC-PPP) and PPP mux in accordance with the following RFCs: 1661, 1662, 1990, 2686, and 3153
- IP support for IPv4 packets including TOS, TTL, and header checksum processing
- Ethernet over first mile IEEE 802.3ah
- Shim header
- Ethernet-to-Ethernet/AAL5/AAL2 inter-working
- L2 Ethernet switching using MAC address or IEEE Std. 802.1P/Q™ VLAN tags
- ATM (AAL2/AAL5) to Ethernet (IP) interworking in accordance with RFC2684 including bridging of ATM ports to Ethernet ports
- Extensive support for ATM statistics and Ethernet RMON/MIB statistics
- AAL2 protocol rate up to 4 CPS at OC-3/STM-1 rate
- Packet over Sonet (POS) up to 622-Mbps full-duplex 124 MultiPHY
- POS hardware; microcode must be loaded as an IRAM package
- Transparent up to 70-Mbps full-duplex
- HDLC up to 70-Mbps full-duplex
- HDLC BUS up to 10 Mbps
- Asynchronous HDLC
- UART
- BISYNC up to 2 Mbps
- User-programmable Virtual FIFO size
- QUICC multichannel controller (QMC) for 64 TDM channels
- One multichannel communication controller (MCC) only on the MPC8360E supporting the following:
  - 256 HDLC or transparent channels
  - 128 SS7 channels
  - Almost any combination of subgroups can be multiplexed to single or multiple TDM interfaces
- Two UTOPIA/POS interfaces on the MPC8360E supporting 124 MultiPHY each (optional 2\*128 MultiPHY with extended address) and one UTOPIA/POS interface on the MPC8358E supporting 31/124 MultiPHY
- Two serial peripheral interfaces (SPI); SPI2 is dedicated to Ethernet PHY management

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<sup>1</sup>.SMII or SGMII media-independent interface is not currently supported.

**Table 1. Absolute Maximum Ratings<sup>1</sup> (continued)**

Characteristic	Symbol	Max Value	Unit	Notes
Storage temperature range	T <sub>STG</sub>	–55 to 150	°C	—

**Notes:**

- Functional and tested operating conditions are given in [Table 2](#). Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
- Caution:** MV<sub>IN</sub> must not exceed GV<sub>DD</sub> by more than 0.3 V. This limit may be exceeded for a maximum of 100 ms during power-on reset and power-down sequences.
- Caution:** OV<sub>IN</sub> must not exceed OV<sub>DD</sub> by more than 0.3 V. This limit may be exceeded for a maximum of 100 ms during power-on reset and power-down sequences.
- Caution:** LV<sub>IN</sub> must not exceed LV<sub>DD</sub> by more than 0.3 V. This limit may be exceeded for a maximum of 100 ms during power-on reset and power-down sequences.
- (M,L,O)V<sub>IN</sub> and MV<sub>REF</sub> may overshoot/undershoot to a voltage and for a maximum duration as shown in [Figure 3](#).
- OV<sub>IN</sub> on the PCI interface may overshoot/undershoot according to the PCI Electrical Specification for 3.3-V operation, as shown in [Figure 4](#).

## 2.1.2 Power Supply Voltage Specification

This table provides the recommended operating conditions for the device. Note that the values in this table are the recommended and tested operating conditions. Proper device operation outside of these conditions is not guaranteed.

**Table 2. Recommended Operating Conditions**

Characteristic	Symbol	Recommended Value	Unit	Notes
Core and PLL supply voltage for  MPC8358 Device Part Number with Processor Frequency label of AD=266MHz and AG=400MHz & QUICC Engine Frequency label of E=300MHz & G=400MHz  MPC8360 Device Part Number with Processor Frequency label of AG=400MHz and AJ=533MHz & QUICC Engine Frequency label of G=400MHz	V <sub>DD</sub> & AV <sub>DD</sub>	1.2 V ± 60 mV	V	1, 3
Core and PLL supply voltage for  MPC8360 Device Part Number with Processor Frequency label of AL=667MHz and QUICC Engine Frequency label of H=500MHz	V <sub>DD</sub> & AV <sub>DD</sub>	1.3 V ± 50 mV	V	1, 3
DDR and DDR2 DRAM I/O supply voltage  DDR DDR2	GV <sub>DD</sub>	2.5 V ± 125 mV 1.8 V ± 90 mV	V	—
Three-speed Ethernet I/O supply voltage	LV <sub>DD0</sub>	3.3 V ± 330 mV 2.5 V ± 125 mV	V	—
Three-speed Ethernet I/O supply voltage	LV <sub>DD1</sub>	3.3 V ± 330 mV 2.5 V ± 125 mV	V	—
Three-speed Ethernet I/O supply voltage	LV <sub>DD2</sub>	3.3 V ± 330 mV 2.5 V ± 125 mV	V	—

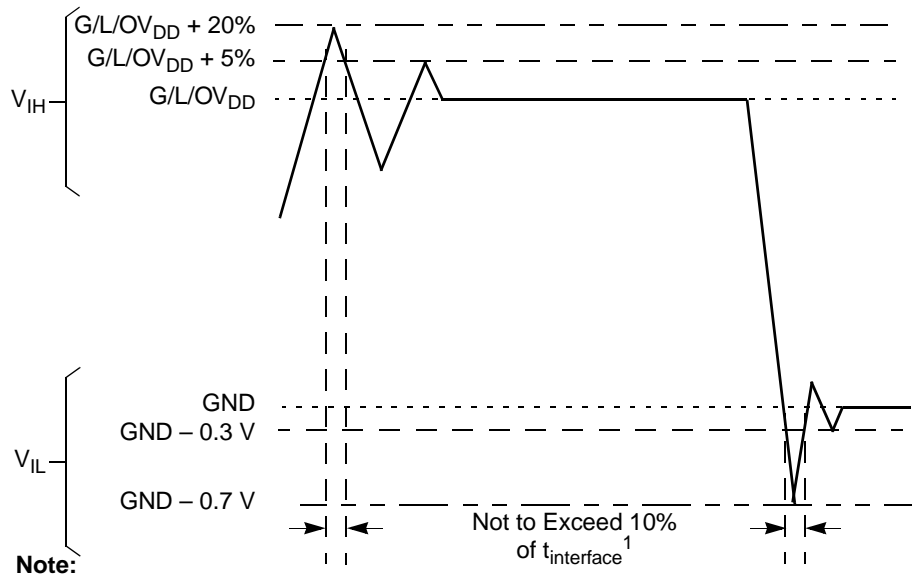
Table 2. Recommended Operating Conditions (continued)

Characteristic	Symbol	Recommended Value	Unit	Notes
PCI, local bus, DUART, system control and power management, I <sup>2</sup> C, SPI, and JTAG I/O voltage	OV <sub>DD</sub>	3.3 V ± 330 mV	V	—
Junction temperature	T <sub>J</sub>	0 to 105 –40 to 105	°C	2

**Notes:**

1. GV<sub>DD</sub>, LV<sub>DD</sub>, OV<sub>DD</sub>, AV<sub>DD</sub>, and V<sub>DD</sub> must track each other and must vary in the same direction—either in the positive or negative direction.
2. The operating conditions for junction temperature, T<sub>J</sub>, on the 600/333/400 MHz and 500/333/500 MHz on rev. 2.0 silicon is 0° to 70 °C. Refer to Errata General9 in *Chip Errata for the MPC8360E, Rev. 1*.
3. For more information on Part Numbering, refer to [Table 80](#).

This figure shows the undershoot and overshoot voltages at the interfaces of the device.


Figure 3. Overshoot/Undershoot Voltage for GV<sub>DD</sub>/OV<sub>DD</sub>/LV<sub>DD</sub>

## 5.2 RESET AC Electrical Characteristics

This section describes the AC electrical specifications for the reset initialization timing requirements of the device. This table provides the reset initialization AC timing specifications for the DDR SDRAM component(s).

**Table 11. RESET Initialization Timing Specifications**

Parameter/Condition	Min	Max	Unit	Notes
Required assertion time of $\overline{\text{HRESET}}$ or $\overline{\text{SRESET}}$ (input) to activate reset flow	32	—	$t_{\text{PCI\_SYNC\_IN}}$	1
Required assertion time of $\overline{\text{PORESET}}$ with stable clock applied to CLKIN when the device is in PCI host mode	32	—	$t_{\text{CLKIN}}$	2
Required assertion time of $\overline{\text{PORESET}}$ with stable clock applied to PCI_SYNC_IN when the device is in PCI agent mode	32	—	$t_{\text{PCI\_SYNC\_IN}}$	1
$\overline{\text{HRESET}}/\overline{\text{SRESET}}$ assertion (output)	512	—	$t_{\text{PCI\_SYNC\_IN}}$	1
$\overline{\text{HRESET}}$ negation to $\overline{\text{SRESET}}$ negation (output)	16	—	$t_{\text{PCI\_SYNC\_IN}}$	1
Input setup time for POR config signals (CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV) with respect to negation of $\overline{\text{PORESET}}$ when the device is in PCI host mode	4	—	$t_{\text{CLKIN}}$	2
Input setup time for POR config signals (CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV) with respect to negation of $\overline{\text{PORESET}}$ when the device is in PCI agent mode	4	—	$t_{\text{PCI\_SYNC\_IN}}$	1
Input hold time for POR config signals with respect to negation of $\overline{\text{HRESET}}$	0	—	ns	—
Time for the device to turn off POR config signals with respect to the assertion of $\overline{\text{HRESET}}$	—	4	ns	3
Time for the device to turn on POR config signals with respect to the negation of $\overline{\text{HRESET}}$	1	—	$t_{\text{PCI\_SYNC\_IN}}$	1, 3

**Notes:**

1.  $t_{\text{PCI\_SYNC\_IN}}$  is the clock period of the input clock applied to PCI\_SYNC\_IN. When the device is in PCI host mode the primary clock is applied to the CLKIN input, and PCI\_SYNC\_IN period depends on the value of CFG\_CLKIN\_DIV. Refer *MPC8360E PowerQUICC II Pro Integrated Communications Processor Reference Manual* for more details.
2.  $t_{\text{CLKIN}}$  is the clock period of the input clock applied to CLKIN. It is only valid when the device is in PCI host mode. Refer *MPC8360E PowerQUICC II Pro Integrated Communications Processor Reference Manual* for more details.
3. POR config signals consists of CFG\_RESET\_SOURCE[0:2] and CFG\_CLKIN\_DIV.

This table provides the PLL and DLL lock times.

**Table 12. PLL and DLL Lock Times**

Parameter/Condition	Min	Max	Unit	Notes
PLL lock times	—	100	$\mu\text{s}$	—
DLL lock times	7680	122,880	csb_clk cycles	1, 2

**Notes:**

1. DLL lock times are a function of the ratio between the output clock and the coherency system bus clock (csb\_clk). A 2:1 ratio results in the minimum and an 8:1 ratio results in the maximum.
2. The csb\_clk is determined by the CLKIN and system PLL ratio. See [Section 21, "Clocking,"](#) for more information.

This table provides the input AC timing specifications for the DDR SDRAM interface when  $GV_{DD}(\text{typ}) = 2.5 \text{ V}$ .

**Table 19. DDR SDRAM Input AC Timing Specifications**

At recommended operating conditions with  $GV_{DD}$  of  $2.5 \text{ V} \pm 5\%$ .

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	$V_{IL}$	—	$MV_{REF} - 0.31$	V	—
AC input high voltage	$V_{IH}$	$MV_{REF} + 0.31$	—	V	—

**Table 20. DDR and DDR2 SDRAM Input AC Timing Specifications Mode**

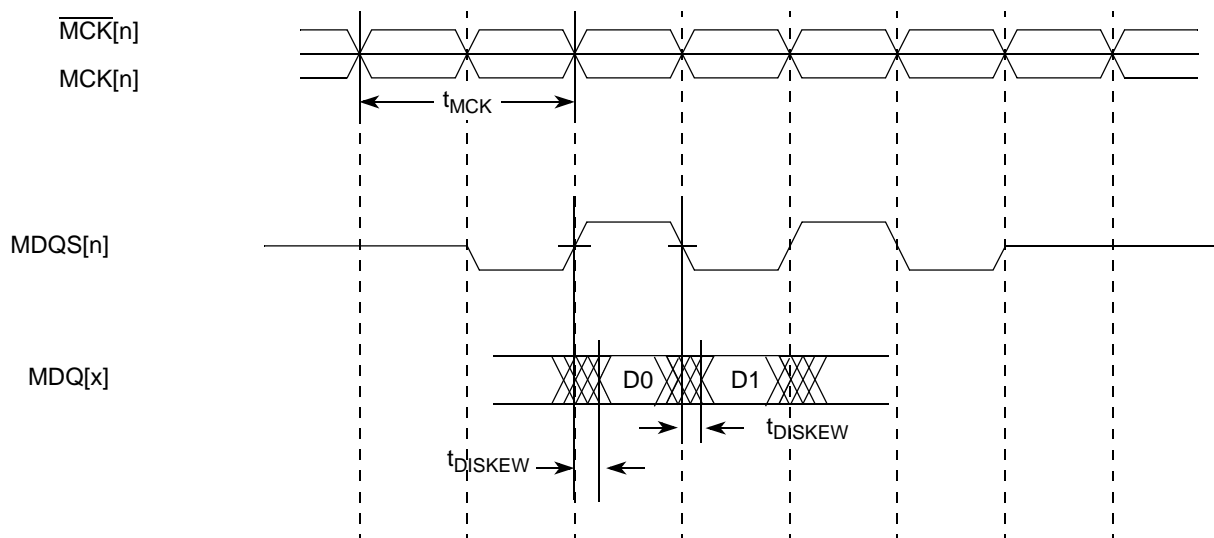
At recommended operating conditions with  $GV_{DD}$  of  $(1.8 \text{ or } 2.5 \text{ V}) \pm 5\%$ .

Parameter	Symbol	Min	Max	Unit	Notes
MDQS—MDQ/MECC input skew per byte 333 MHz 266 MHz 200 MHz	$t_{DISKEW}$	—750 —1125 —1250	750 1125 1250	ps	1, 2

**Notes:**

- AC timing values are based on the DDR data rate, which is twice the DDR memory bus frequency.
- Maximum possible skew between a data strobe ( $MDQS[n]$ ) and any corresponding bit of data ( $MDQ[8n + \{0...7\}]$  if  $0 \leq n \leq 7$ ) or ECC ( $MECC[\{0...7\}]$  if  $n = 8$ ).

This figure shows the input timing diagram for the DDR controller.



**Figure 6. DDR Input Timing Diagram**

**Table 21. DDR and DDR2 SDRAM Output AC Timing Specifications for Source Synchronous Mode (continued)**

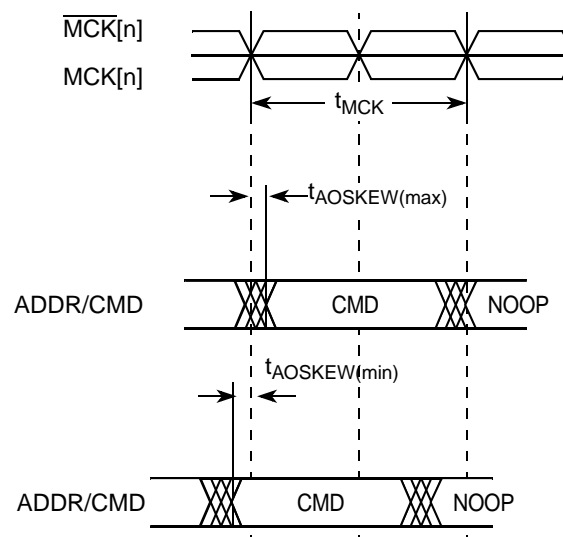
At recommended operating conditions with  $GV_{DD}$  of (1.8 V or 2.5 V)  $\pm$  5%.

Parameter <sup>8</sup>	Symbol <sup>1</sup>	Min	Max	Unit	Notes
MDQS epilogue end	$t_{DDKHME}$	-0.6	0.9	ns	7

**Notes:**

- The symbols used for timing specifications follow the pattern of  $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$  for inputs and  $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$  for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example,  $t_{DDKHAS}$  symbolizes DDR timing (DD) for the time  $t_{MCK}$  memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also,  $t_{DDKLDX}$  symbolizes DDR timing (DD) for the time  $t_{MCK}$  memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
- All MCK/ $\overline{MCK}$  referenced measurements are made from the crossing of the two signals  $\pm 0.1$  V.
- In the source synchronous mode, MCK/ $\overline{MCK}$  can be shifted in  $\frac{1}{4}$  applied cycle increments through the clock control register. For the skew measurements referenced for  $t_{AOSKEW}$  it is assumed that the clock adjustment is set to align the address/command valid with the rising edge of MCK.
- ADDR/CMD includes all DDR SDRAM output signals except  $\overline{MCK}/\overline{MCK}$ ,  $\overline{MCS}$ , and MDQ/MECC/MDM/MDQS. For the ADDR/CMD setup and hold specifications, it is assumed that the clock control register is set to adjust the memory clocks by  $\frac{1}{2}$  applied cycle.
- Note that  $t_{DDKMHM}$  follows the symbol conventions described in note 1. For example,  $t_{DDKMHM}$  describes the DDR timing (DD) from the rising edge of the MCK(n) clock (KH) until the MDQS signal is valid (MH).  $t_{DDKMHM}$  can be modified through control of the DQSS override bits in the TIMING\_CFG\_2 register. In source synchronous mode, this is typically set to the same delay as the clock adjust in the CLK\_CNTL register. The timing parameters listed in the table assume that these two parameters have been set to the same adjustment value. Refer *MPC8360E PowerQUICC II Pro Integrated Communications Processor Reference Manual* for a description and understanding of the timing modifications enabled by use of these bits.
- Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the device.
- All outputs are referenced to the rising edge of MCK(n) at the pins of the device. Note that  $t_{DDKHMP}$  follows the symbol conventions described in note 1.
- AC timing values are based on the DDR data rate, which is twice the DDR memory bus frequency.
- In rev. 2.0 silicon,  $t_{DDKMHM}$  maximum meets the specification of 0.6 ns. In rev. 2.0 silicon, due to errata,  $t_{DDKMHM}$  minimum is -0.9 ns. Refer to Errata DDR18 in *Chip Errata for the MPC8360E, Rev. 1*.

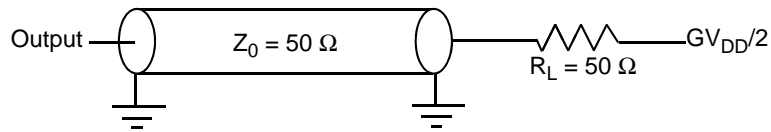
This figure shows the DDR SDRAM output timing for address skew with respect to any MCK.



**Figure 7. Timing Diagram for  $t_{AOSKEW}$  Measurement**



This figure provides the AC test load for the DDR bus.



**Figure 8. DDR AC Test Load**

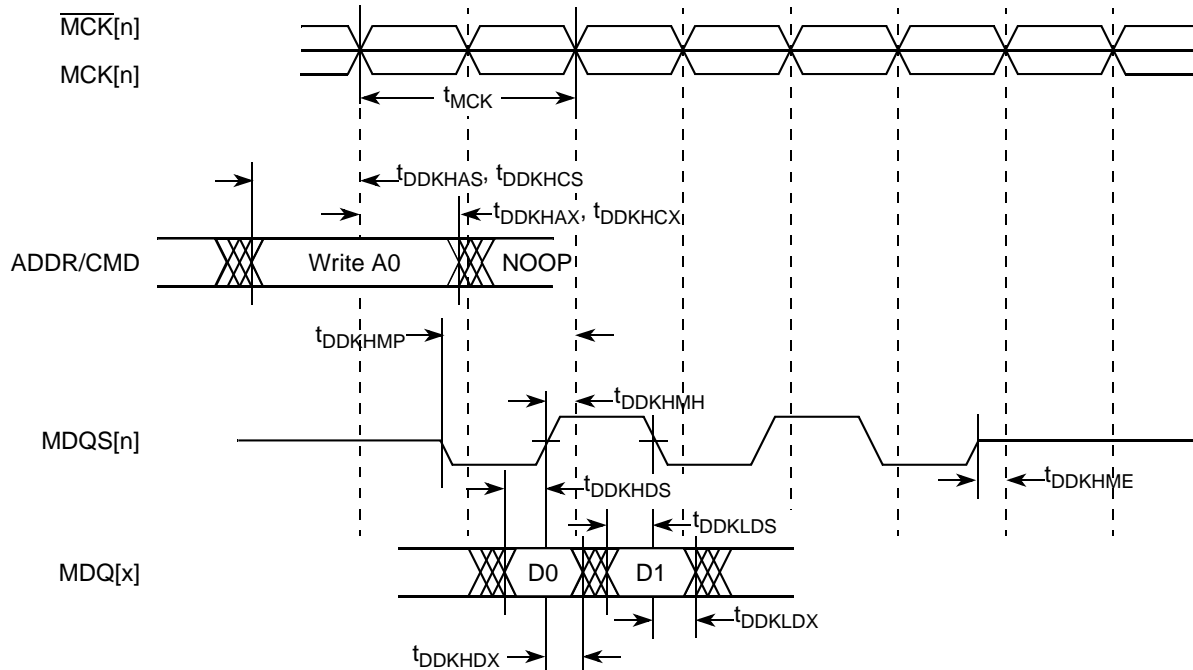
**Table 22. DDR and DDR2 SDRAM Measurement Conditions**

Symbol	DDR	DDR2	Unit	Notes
$V_{TH}$	$MV_{REF} \pm 0.31\text{ V}$	$MV_{REF} \pm 0.25\text{ V}$	V	1
$V_{OUT}$	$0.5 \times GV_{DD}$	$0.5 \times GV_{DD}$	V	2

**Notes:**

1. Data input threshold measurement point.
2. Data output measurement point.

This figure shows the DDR SDRAM output timing diagram for source synchronous mode.



**Figure 9. DDR SDRAM Output Timing Diagram for Source Synchronous Mode**

## 7 DUART

This section describes the DC and AC electrical specifications for the DUART interface of the MPC8360E/58E.

### 7.1 DUART DC Electrical Characteristics

This table provides the DC electrical characteristics for the DUART interface of the device.

**Table 23. DUART DC Electrical Characteristics**

Parameter	Symbol	Min	Max	Unit	Notes
High-level input voltage	$V_{IH}$	2	$OV_{DD} + 0.3$	V	—
Low-level input voltage $OV_{DD}$	$V_{IL}$	-0.3	0.8	V	—
High-level output voltage, $I_{OH} = -100 \mu A$	$V_{OH}$	$OV_{DD} - 0.4$	—	V	—
Low-level output voltage, $I_{OL} = 100 \mu A$	$V_{OL}$	—	0.2	V	—
Input current ( $0 V \leq V_{IN} \leq OV_{DD}$ )	$I_{IN}$	—	$\pm 10$	$\mu A$	1

**Note:**

- Note that the symbol  $V_{IN}$ , in this case, represents the  $OV_{IN}$  symbol referenced in [Table 1](#) and [Table 2](#).

### 7.2 DUART AC Electrical Specifications

This table provides the AC timing parameters for the DUART interface of the device.

**Table 24. DUART AC Timing Specifications**

Parameter	Value	Unit	Notes
Minimum baud rate	256	baud	—
Maximum baud rate	>1,000,000	baud	1
Oversample rate	16	—	2

**Notes:**

- Actual attainable baud rate is limited by the latency of interrupt processing.
- The middle of a start bit is detected as the eighth sampled 0 after the 1-to-0 transition of the start bit. Subsequent bit values are sampled each sixteenth sample.

## 8 UCC Ethernet Controller: Three-Speed Ethernet, MII Management

This section provides the AC and DC electrical characteristics for three-speed, 10/100/1000, and MII management.

### 8.1 Three-Speed Ethernet Controller (10/100/1000 Mbps)—GMII/MII/RMII/TBI/RGMII/RTBI Electrical Characteristics

The electrical characteristics specified here apply to all GMII (gigabit media independent interface), MII (media independent interface), RMII (reduced media independent interface), TBI (ten-bit interface), RGMII (reduced gigabit media independent interface), and RTBI (reduced ten-bit interface) signals except MDIO (management data input/output) and MDC (management data clock). The MII, RMII, GMII, and TBI interfaces are only defined for 3.3 V, while the RGMII and RTBI interfaces are only defined for 2.5 V. The RGMII and RTBI interfaces follow the Hewlett-Packard reduced pin-count interface for Gigabit Ethernet

### 8.2.1.1 GMII Transmit AC Timing Specifications

This table provides the GMII transmit AC timing specifications.

**Table 27. GMII Transmit AC Timing Specifications**

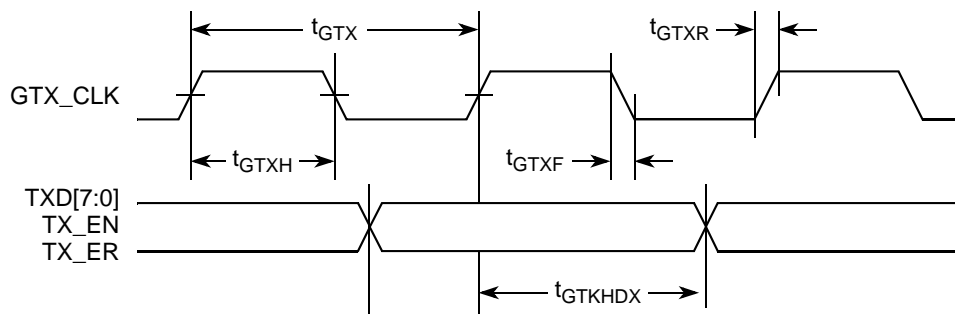
At recommended operating conditions with  $V_{DD}/OV_{DD}$  of  $3.3\text{ V} \pm 10\%$ .

Parameter/Condition	Symbol <sup>1</sup>	Min	Typ	Max	Unit	Notes
GTX_CLK clock period	$t_{GTX}$	—	8.0	—	ns	—
GTX_CLK duty cycle	$t_{GTXH}/t_{GTX}$	40	—	60	%	—
GTX_CLK to GMII data TXD[7:0], TX_ER, TX_EN delay	$t_{GTKHDX}$ $t_{GTKHDV}$	0.5 —	—	— 5.0	ns	3
GTX_CLK clock rise time, (20% to 80%)	$t_{GTXR}$	—	—	1.0	ns	—
GTX_CLK clock fall time, (80% to 20%)	$t_{GTXF}$	—	—	1.0	ns	—
GTX_CLK125 clock period	$t_{G125}$	—	8.0	—	ns	2
GTX_CLK125 reference clock duty cycle measured at $V_{DD}/2$	$t_{G125H}/t_{G125}$	45	—	55	%	2

**Notes:**

1. The symbols used for timing specifications follow the pattern  $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$  for inputs and  $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$  for outputs. For example,  $t_{GTKHDV}$  symbolizes GMII transmit timing (GT) with respect to the  $t_{GTX}$  clock reference (K) going to the high state (H) relative to the time date input signals (D) reaching the valid state (V) to state or setup time. Also,  $t_{GTKHDX}$  symbolizes GMII transmit timing (GT) with respect to the  $t_{GTX}$  clock reference (K) going to the high state (H) relative to the time date input signals (D) going invalid (X) or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of  $t_{GTX}$  represents the GMII(G) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. This symbol is used to represent the external GTX\_CLK125 signal and does not follow the original symbol naming convention.
3. In rev. 2.0 silicon, due to errata,  $t_{GTKHDX}$  minimum and  $t_{GTKHDV}$  maximum are not supported when the GTX\_CLK is selected. Refer to Errata *QE\_ENET18* in *Chip Errata for the MPC8360E, Rev. 1*.

This figure shows the GMII transmit AC timing diagram.



**Figure 10. GMII Transmit AC Timing Diagram**

## 8.2.5 RGMII and RTBI AC Timing Specifications

This table presents the RGMII and RTBI AC timing specifications.

**Table 35. RGMII and RTBI AC Timing Specifications**

At recommended operating conditions with  $V_{DD}$  of 2.5 V  $\pm$  5%.

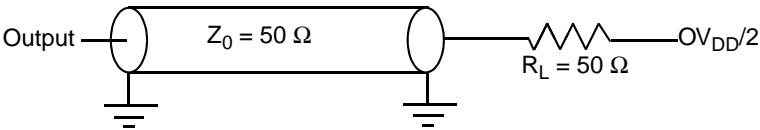
Parameter/Condition	Symbol <sup>1</sup>	Min	Typ	Max	Unit	Notes
Data to clock output skew (at transmitter)	$t_{SKRGTKHDX}$ $t_{SKRGTKHDV}$	−0.5 —	—	— 0.5	ns	7
Data to clock input skew (at receiver)	$t_{SKRGDXKH}$ $t_{SKRGDVKH}$	1.0 —	—	— 2.6	ns	2
Clock cycle duration	$t_{RGT}$	7.2	8.0	8.8	ns	3
Duty cycle for 1000Base-T	$t_{RGTH}/t_{RGT}$	45	50	55	%	4, 5
Duty cycle for 10BASE-T and 100BASE-TX	$t_{RGTH}/t_{RGT}$	40	50	60	%	3, 5
Rise time (20–80%)	$t_{RGTR}$	—	—	0.75	ns	—
Fall time (20–80%)	$t_{RGTF}$	—	—	0.75	ns	—
GTX_CLK125 reference clock period	$t_{G125}$	—	8.0	—	ns	6
GTX_CLK125 reference clock duty cycle	$t_{G125H}/t_{G125}$	47	—	53	%	—

**Notes:**

- Note that, in general, the clock reference symbol representation for this section is based on the symbols RGT to represent RGMII and RTBI timing. For example, the subscript of  $t_{RGT}$  represents the TBI (T) receive (Rx) clock. Note also that the notation for rise (R) and fall (F) times follows the clock symbol that is being represented. For symbols representing skews, the subscript is skew (SK) followed by the clock that is being skewed (RGT).
- This implies that PC board design requires clocks to be routed such that an additional trace delay of greater than 1.5 ns can be added to the associated clock signal.
- For 10 and 100 Mbps,  $t_{RGT}$  scales to 400 ns  $\pm$  40 ns and 40 ns  $\pm$  4 ns, respectively.
- Duty cycle may be stretched/shrunk during speed changes or while transitioning to a received packet's clock domains as long as the minimum duty cycle is not violated and stretching occurs for no more than three  $t_{RGT}$  of the lowest speed transitioned between.
- Duty cycle reference is  $V_{DD}/2$ .
- This symbol is used to represent the external GTX\_CLK125 and does not follow the original symbol naming convention.
- In rev. 2.0 silicon, due to errata,  $t_{SKRGTKHDX}$  minimum is −2.3 ns and  $t_{SKRGTKHDV}$  maximum is 1 ns for UCC1, 1.2 ns for UCC2 option 1, and 1.8 ns for UCC2 option 2. In rev. 2.1 silicon, due to errata,  $t_{SKRGTKHDX}$  minimum is −0.65 ns for UCC2 option 1 and −0.9 for UCC2 option 2, and  $t_{SKRGTKHDV}$  maximum is 0.75 ns for UCC1 and UCC2 option 1 and 0.85 for UCC2 option 2. Refer to Errata QE\_ENET10 in *Chip Errata for the MPC8360E, Rev. 1*. UCC1 does meet  $t_{SKRGTKHDX}$  minimum for rev. 2.1 silicon.

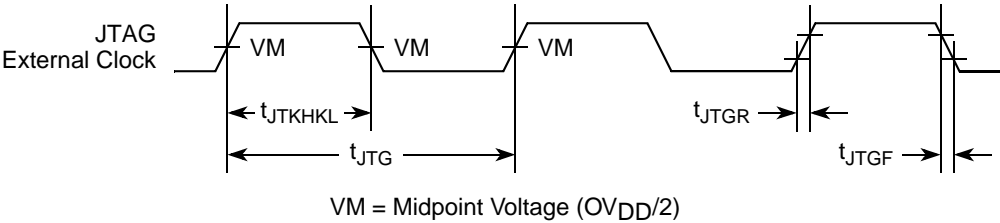
# JTAG AC Electrical Characteristics

This figure provides the AC test load for TDO and the boundary-scan outputs of the device.



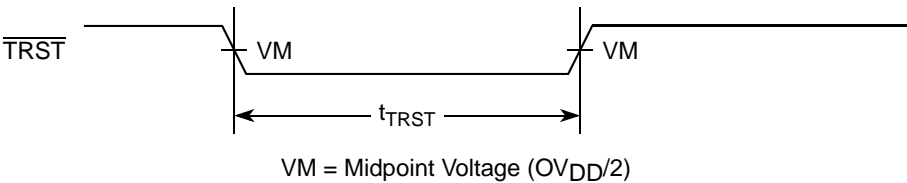
**Figure 29. AC Test Load for the JTAG Interface**

This figure provides the JTAG clock input timing diagram.



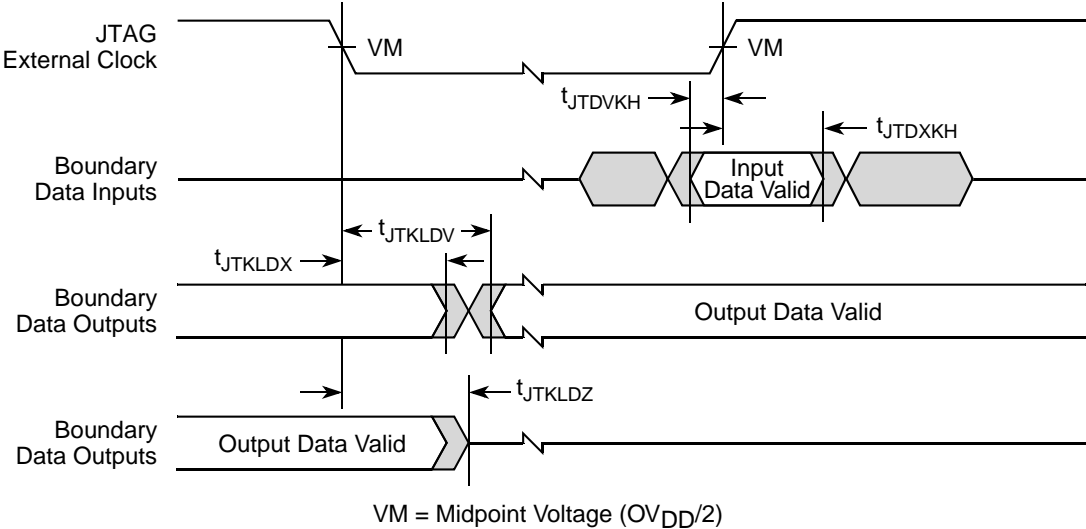
**Figure 30. JTAG Clock Input Timing Diagram**

This figure provides the  $\overline{\text{TRST}}$  timing diagram.



**Figure 31.  $\overline{\text{TRST}}$  Timing Diagram**

This figure provides the boundary-scan timing diagram.



**Figure 32. Boundary-Scan Timing Diagram**

## 14.2 GPIO AC Timing Specifications

This table provides the GPIO input and output AC timing specifications.

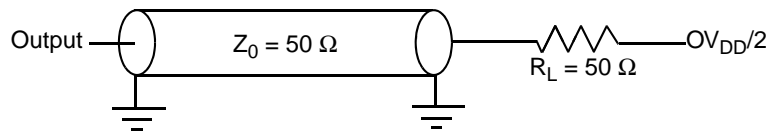
**Table 52. GPIO Input AC Timing Specifications<sup>1</sup>**

Characteristic	Symbol <sup>2</sup>	Typ	Unit
GPIO inputs—minimum pulse width	$t_{PIWD}$	20	ns

**Notes:**

1. Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of CLKIN. Timings are measured at the pin.
2. GPIO inputs and outputs are asynchronous to any visible clock. GPIO outputs should be synchronized before use by any external synchronous logic. GPIO inputs are required to be valid for at least  $t_{PIWD}$  ns to ensure proper operation.

This figure provides the AC test load for the GPIO.



**Figure 40. GPIO AC Test Load**

## 15 IPIC

This section describes the DC and AC electrical specifications for the external interrupt pins of the MPC8360E/58E.

### 15.1 IPIC DC Electrical Characteristics

This table provides the DC electrical characteristics for the external interrupt pins of the IPIC.

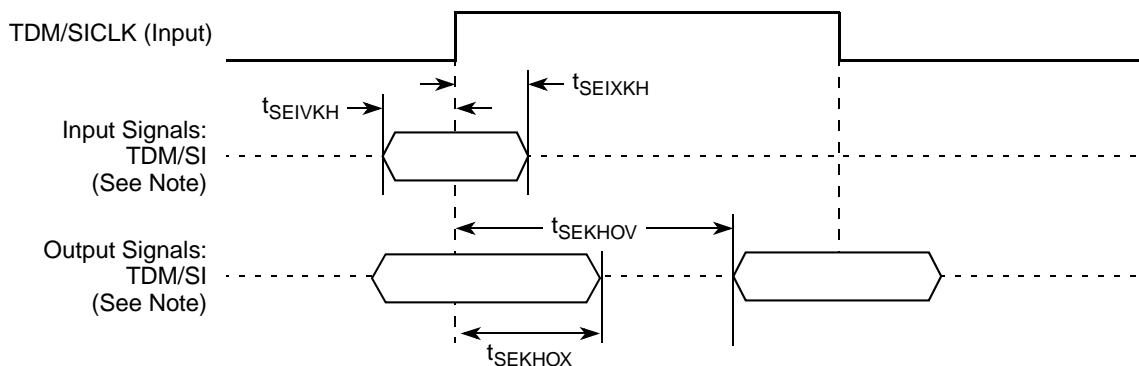
**Table 53. IPIC DC Electrical Characteristics**

Characteristic	Symbol	Condition	Min	Max	Unit
Input high voltage	$V_{IH}$	—	2.0	$OV_{DD} + 0.3$	V
Input low voltage	$V_{IL}$	—	-0.3	0.8	V
Input current	$I_{IN}$	—	—	$\pm 10$	$\mu A$
Output low voltage	$V_{OL}$	$I_{OL} = 6.0 \text{ mA}$	—	0.5	V
Output low voltage	$V_{OL}$	$I_{OL} = 3.2 \text{ mA}$	—	0.4	V

**Notes:**

1. This table applies for pins  $\overline{IRQ}[0:7]$ ,  $\overline{IRQ\_OUT}$ ,  $\overline{MCP\_OUT}$ , and CE ports Interrupts.
2.  $\overline{IRQ\_OUT}$  and  $\overline{MCP\_OUT}$  are open drain pins, thus  $V_{OH}$  is not relevant for those pins.

This figure shows the TDM/SI timing with external clock.



**Note:** The clock edge is selectable on TDM/SI

**Figure 45. TDM/SI AC Timing (External Clock) Diagram**

## 17.3 UTOPIA/POS

This section describes the DC and AC electrical specifications for the UTOPIA/POS of the MPC8360E/58E.

## 17.4 UTOPIA/POS DC Electrical Characteristics

This table provides the DC electrical characteristics for the device UTOPIA.

**Table 59. UTOPIA DC Electrical Characteristics**

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	$V_{OH}$	$I_{OH} = -8.0 \text{ mA}$	2.4	—	V
Output low voltage	$V_{OL}$	$I_{OL} = 8.0 \text{ mA}$	—	0.5	V
Input high voltage	$V_{IH}$	—	2.0	$OV_{DD} + 0.3$	V
Input low voltage	$V_{IL}$	—	-0.3	0.8	V
Input current	$I_{IN}$	$0 \text{ V} \leq V_{IN} \leq OV_{DD}$	—	$\pm 10$	$\mu\text{A}$

## 17.5 UTOPIA/POS AC Timing Specifications

This table provides the UTOPIA input and output AC timing specifications.

**Table 60. UTOPIA AC Timing Specifications<sup>1</sup>**

Characteristic	Symbol <sup>2</sup>	Min	Max	Unit	Notes
UTOPIA outputs—Internal clock delay	$t_{UIKHOV}$	0	11.5	ns	—
UTOPIA outputs—External clock delay	$t_{UEKHOV}$	1	11.6	ns	—
UTOPIA outputs—Internal clock high impedance	$t_{UIKHOX}$	0	8.0	ns	—
UTOPIA outputs—External clock high impedance	$t_{UEKHOX}$	1	10.0	ns	—
UTOPIA inputs—Internal clock input setup time	$t_{UIIVKH}$	6	—	ns	—
UTOPIA inputs—External clock input setup time	$t_{UEIVKH}$	4	—	ns	3

# 20.2 Mechanical Dimensions of the TBGA Package

This figure depicts the mechanical dimensions and bottom surface nomenclature of the device, 740-TBGA package.

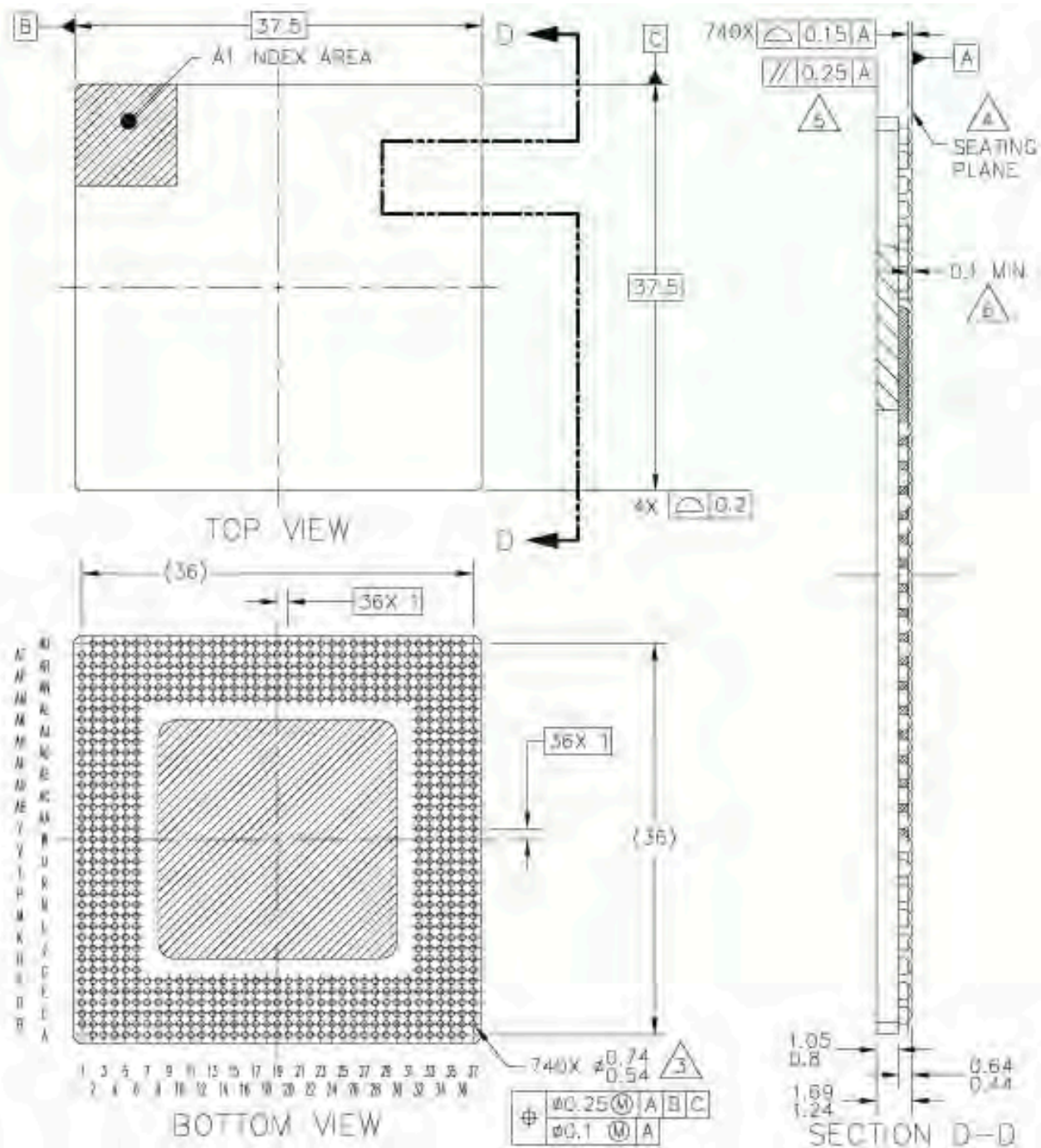


Figure 53. Mechanical Dimensions and Bottom Surface Nomenclature of the TBGA Package



**Table 66. MPC8360E TBGA Pinout Listing (continued)**

Signal	Package Pin Number	Pin Type	Power Supply	Notes
<b>No Connect</b>				
NC	AM20, AU19	—	—	—

**Notes:**

1. This pin is an open drain signal. A weak pull-up resistor (1 k $\Omega$ ) should be placed on this pin to OV<sub>DD</sub>.
2. This pin is an open drain signal. A weak pull-up resistor (2–10 k $\Omega$ ) should be placed on this pin to OV<sub>DD</sub>.
3. This output is actively driven during reset rather than being three-stated during reset.
4. These JTAG pins have weak internal pull-up P-FETs that are always enabled.
5. This pin should have a weak pull up if the chip is in PCI host mode. Follow PCI specifications recommendation.
6. These are On Die Termination pins, used to control DDR2 memories internal termination resistance.
7. This pin must always be tied to GND.
8. This pin must always be left not connected.
9. Refer to *MPC8360E PowerQUICC II Pro Integrated Communications Processor Reference Manual* section on “RGMII Pins,” for information about the two UCC2 Ethernet interface options.
10. It is recommended that MDIC0 be tied to GND using an 18.2  $\Omega$  resistor and MDIC1 be tied to DDR power using an 18.2  $\Omega$  resistor for DDR2.

This table shows the pin list of the MPC8358E TBGA package.

**Table 67. MPC8358E TBGA Pinout Listing**

Signal	Package Pin Number	Pin Type	Power Supply	Notes
<b>DDR SDRAM Memory Controller Interface</b>				
MEMC1_MDQ[0:63]	AJ34, AK33, AL33, AL35, AJ33, AK34, AK32, AM36, AN37, AN35, AR34, AT34, AP37, AP36, AR36, AT35, AP34, AR32, AP32, AM31, AN33, AM34, AM33, AM30, AP31, AM27, AR30, AT32, AN29, AP29, AN27, AR29, AN8, AN7, AM8, AM6, AP9, AN9, AT7, AP7, AU6, AP6, AR4, AR3, AT6, AT5, AR5, AT3, AP4, AM5, AP3, AN3, AN5, AL5, AN4, AM2, AL2, AH5, AK3, AJ2, AJ3, AH4, AK4, AH3	I/O	GV <sub>DD</sub>	—
MEMC_MECC[0:4]/MSRCID[0:4]	AP24, AN22, AM19, AN19, AM24	I/O	GV <sub>DD</sub>	—
MEMC_MECC[5]/MDVAL	AM23	I/O	GV <sub>DD</sub>	—
MEMC_MECC[6:7]	AM22, AN18	I/O	GV <sub>DD</sub>	—
MEMC_MDM[0:8]	AL36, AN34, AP33, AN28, AT9, AU4, AM3, AJ6, AP27	O	GV <sub>DD</sub>	—
MEMC_MDQS[0:8]	AK35, AP35, AN31, AM26, AT8, AU3, AL4, AJ5, AP26	I/O	GV <sub>DD</sub>	—
MEMC_MBA[0:1]	AU29, AU30	O	GV <sub>DD</sub>	—
MEMC_MBA[2]	AT30	O	GV <sub>DD</sub>	—
MEMC_MA[0:14]	AU21, AP22, AP21, AT21, AU25, AU26, AT23, AR26, AU24, AR23, AR28, AU23, AR22, AU20, AR18	O	GV <sub>DD</sub>	—
MEMC_MODT[0:3]	AG33, AJ36, AT1, AK2	O	GV <sub>DD</sub>	6

Table 67. MPC8358E TBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PORESET	L37	I	OV <sub>DD</sub>	—
HRESET	L36	I/O	OV <sub>DD</sub>	1
SRESET	M33	I/O	OV <sub>DD</sub>	2
Thermal Management				
THERM0	AP19	I	GV <sub>DD</sub>	—
THERM1	AT31	I	GV <sub>DD</sub>	—
Power and Ground Signals				
AV <sub>DD</sub> 1	K35	Power for LBIU DLL (1.2 V)	AV <sub>DD</sub> 1	—
AV <sub>DD</sub> 2	K36	Power for CE PLL (1.2 V)	AV <sub>DD</sub> 2	—
AV <sub>DD</sub> 5	AM29	Power for e300 PLL (1.2 V)	AV <sub>DD</sub> 5	—
AV <sub>DD</sub> 6	K37	Power for system PLL (1.2 V)	AV <sub>DD</sub> 6	—
GND	A2, A8, A13, A19, A22, A25, A31, A33, A36, B7, B12, B24, B27, B30, C4, C6, C9, C15, C26, C32, D3, D8, D11, D14, D17, D19, D23, D27, E7, E13, E25, E30, E36, F4, F37, G34, H1, H5, H32, H33, J4, J32, J37, K1, L3, L5, L33, L34, M1, M34, M35, N37, P2, P5, P35, P36, R4, T3, U1, U5, U35, V37, W1, W4, W33, W36, Y34, AA3, AA5, AC3, AC32, AC35, AD1, AD37, AE4, AE34, AE36, AF33, AG4, AG6, AG32, AH35, AJ1, AJ4, AJ32, AJ35, AJ37, AK36, AL3, AL34, AM4, AN6, AN23, AN30, AP8, AP12, AP14, AP16, AP17, AP20, AP25, AR6, AR8, AR9, AR19, AR24, AR31, AR35, AR37, AT4, AT10, AT19, AT20, AT25, AU14, AU22, AU28, AU35	—	—	—
GV <sub>DD</sub>	AD4, AE3, AF1, AF5, AF35, AF37, AG2, AG36, AH33, AH34, AK5, AM1, AM35, AM37, AN2, AN10, AN11, AN12, AN14, AN32, AN36, AP5, AP23, AP28, AR1, AR7, AR10, AR12, AR21, AR25, AR27, AR33, AT15, AT22, AT28, AT33, AU2, AU5, AU16, AU31, AU36	Power for DDR DRAM I/O voltage (2.5 or 1.8 V)	GV <sub>DD</sub>	—
LV <sub>DD</sub> 0	D5, D6	Power for UCC1 Ethernet interface (2.5 V, 3.3 V)	LV <sub>DD</sub> 0	—

**Table 70. System PLL Multiplication Factors (continued)**

RCWL[SPMF]	System PLL Multiplication Factor
1100	× 12
1101	× 13
1110	× 14
1111	× 15

The RCWL[SVCOD] denotes the system PLL VCO internal frequency as shown in this table.

**Table 71. System PLL VCO Divider**

RCWL[SVCOD]	VCO Divider
00	4
01	8
10	2
11	Reserved

### NOTE

The VCO divider must be set properly so that the system VCO frequency is in the range of 600–1400 MHz.

The system VCO frequency is derived from the following equations:

- $csb\_clk = \{PCI\_SYNC\_IN \times (1 + CFG\_CLKIN\_DIV)\} \times SPMF$
- System VCO Frequency =  $csb\_clk \times$  VCO divider (if both RCWL[DDRCM] and RCWL[LBCM] are cleared)  
OR
- System VCO frequency =  $2 \times csb\_clk \times$  VCO divider (if either RCWL[DDRCM] or RCWL[LBCM] are set).

As described in [Section 21, “Clocking,”](#) the LBCM, DDRCM, and SPMF parameters in the reset configuration word low and the CFG\_CLKIN\_DIV configuration input signal select the ratio between the primary clock input (CLKIN or PCI\_CLK) and the internal coherent system bus clock ( $csb\_clk$ ). This table shows the expected frequency values for the CSB frequency for select  $csb\_clk$  to CLKIN/PCI\_SYNC\_IN ratios.

**Table 72. CSB Frequency Options**

CFG_CLKIN_DIV at Reset <sup>1</sup>	SPMF	$csb\_clk$ : Input Clock Ratio <sup>2</sup>	Input Clock Frequency (MHz) <sup>2</sup>			
			16.67	25	33.33	66.67
			$csb\_clk$ Frequency (MHz)			
Low	0010	2:1				133
Low	0011	3:1				200
Low	0100	4:1				266
Low	0101	5:1				333

The QUICC Engine block VCO frequency is derived from the following equations:

$$ce\_clk = (\text{primary clock input} \times \text{CEPMF}) \div (1 + \text{CEPDF})$$

$$\text{QE VCO Frequency} = ce\_clk \times \text{VCO divider} \times (1 + \text{CEPDF})$$

## 21.4 Suggested PLL Configurations

To simplify the PLL configurations, the device might be separated into two clock domains. The first domain contains the CSB PLL and the core PLL. The core PLL is connected serially to the CSB PLL, and has the `csb_clk` as its input clock. The second clock domain has the QUICC Engine block PLL. The clock domains are independent, and each of their PLLs are configured separately. Both of the domains has one common input clock. This table shows suggested PLL configurations for 33 and 66 MHz input clocks and illustrates each of the clock domains separately. Any combination of clock domains setting with same input clock are valid. Refer to [Section 21, “Clocking,”](#) for the appropriate operating frequencies for your device.

**Table 76. Suggested PLL Configurations**

Conf No. <sup>1</sup>	SPMF	CORE PLL	CEPMF	CEPDF	Input Clock Freq (MHz)	CSB Freq (MHz)	Core Freq (MHz)	QUICC Engine Freq (MHz)	400 (MHz)	533 (MHz)	667 (MHz)
<b>33 MHz CLKIN/PCI_SYNC_IN Options</b>											
s1	0100	0000100	æ	æ	33	133	266	—	∞	∞	∞
s2	0100	0000101	æ	æ	33	133	333	—	∞	∞	∞
s3	0101	0000100	æ	æ	33	166	333	—	∞	∞	∞
s4	0101	0000101	æ	æ	33	166	416	—	—	∞	∞
s5	0110	0000100	æ	æ	33	200	400	—	∞	∞	∞
s6	0110	0000110	æ	æ	33	200	600	—	—	—	∞
s7	0111	0000011	æ	æ	33	233	350	—	∞	∞	∞
s8	0111	0000100	æ	æ	33	233	466	—	—	∞	∞
s9	0111	0000101	æ	æ	33	233	583	—	—	—	∞
s10	1000	0000011	æ	æ	33	266	400	—	∞	∞	∞
s11	1000	0000100	æ	æ	33	266	533	—	—	∞	∞
s12	1000	0000101	æ	æ	33	266	667	—	—	—	∞
s13	1001	0000010	æ	æ	33	300	300	—	∞	∞	∞
s14	1001	0000011	æ	æ	33	300	450	—	—	∞	∞
s15	1001	0000100	æ	æ	33	300	600	—	—	—	∞
s16	1010	0000010	æ	æ	33	333	333	—	∞	∞	∞
s17	1010	0000011	æ	æ	33	333	500	—	—	∞	∞
s18	1010	0000100	æ	æ	33	333	667	—	—	—	∞
c1	æ	æ	01001	0	33	—	—	300	∞	∞	∞
c2	æ	æ	01100	0	33	—	—	400	∞	∞	∞
c3	æ	æ	01110	0	33	—	—	466	—	∞	∞
c4	æ	æ	01111	0	33	—	—	500	—	∞	∞

**Table 77. Package Thermal Characteristics for the TBGA Package (continued)**

Characteristic	Symbol	Value	Unit	Notes
Junction-to-package natural convection on top	$\Psi_{JT}$	1	°C/W	6

**Notes**

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, airflow, power dissipation of other components on the board, and board thermal resistance.
2. Per JEDEC JESD51-2 and SEMI G38-87 with the single layer board horizontal.
3. Per JEDEC JESD51-6 with the board horizontal. 1 m/sec is approximately equal to 200 linear feet per minute (LFM).
4. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

## 22.2 Thermal Management Information

For the following sections,  $P_D = (V_{DD} \times I_{DD}) + P_{I/O}$  where  $P_{I/O}$  is the power dissipation of the I/O drivers. See [Table 6](#) for typical power dissipations values.

### 22.2.1 Estimation of Junction Temperature with Junction-to-Ambient Thermal Resistance

An estimation of the chip junction temperature,  $T_J$ , can be obtained from the equation:

$$T_J = T_A + (R_{\theta JA} \times P_D)$$

where:

$T_J$  = junction temperature (°C)

$T_A$  = ambient temperature for the package (°C)

$R_{\theta JA}$  = junction-to-ambient thermal resistance (°C/W)

$P_D$  = power dissipation in the package (W)

The junction-to-ambient thermal resistance is an industry standard value that provides a quick and easy estimation of thermal performance. As a general statement, the value obtained on a single-layer board is appropriate for a tightly packed printed-circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low power dissipation and the components are well separated. Test cases have demonstrated that errors of a factor of two (in the quantity  $T_J - T_A$ ) are possible.

### 22.2.2 Estimation of Junction Temperature with Junction-to-Board Thermal Resistance

The thermal performance of a device cannot be adequately predicted from the junction-to-ambient thermal resistance. The thermal performance of any component is strongly dependent on the power dissipation of surrounding components. Additionally, the ambient temperature varies widely within the application. For many natural convection and especially closed box applications, the board temperature at the perimeter (edge) of the package is approximately the same as the local air temperature near the device. Specifying the local ambient conditions explicitly as the board temperature provides a more precise description of the local ambient conditions that determine the temperature of the device. At a known board temperature, the junction temperature is estimated using the following equation: